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#### **Applications of Embedded - FPGAs**

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Active
Number of LABs/CLBs	2125
Number of Logic Elements/Cells	17000
Total RAM Bits	716800
Number of I/O	116
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	328-LFBGA, CSBGA
Supplier Device Package	328-CSBGA (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe3-17ea-7mg328i

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# LatticeECP3 Family Data Sheet Architecture

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Data Sheet DS1021

## **Architecture Overview**

Each LatticeECP3 device contains an array of logic blocks surrounded by Programmable I/O Cells (PIC). Interspersed between the rows of logic blocks are rows of sysMEM<sup>™</sup> Embedded Block RAM (EBR) and rows of sys-DSP<sup>™</sup> Digital Signal Processing slices, as shown in Figure 2-1. The LatticeECP3-150 has four rows of DSP slices; all other LatticeECP3 devices have two rows of DSP slices. In addition, the LatticeECP3 family contains SERDES Quads on the bottom of the device.

There are two kinds of logic blocks, the Programmable Functional Unit (PFU) and Programmable Functional Unit without RAM (PFF). The PFU contains the building blocks for logic, arithmetic, RAM and ROM functions. The PFF block contains building blocks for logic, arithmetic and ROM functions. Both PFU and PFF blocks are optimized for flexibility, allowing complex designs to be implemented quickly and efficiently. Logic Blocks are arranged in a two-dimensional array. Only one type of block is used per row.

The LatticeECP3 devices contain one or more rows of sysMEM EBR blocks. sysMEM EBRs are large, dedicated 18Kbit fast memory blocks. Each sysMEM block can be configured in a variety of depths and widths as RAM or ROM. In addition, LatticeECP3 devices contain up to two rows of DSP slices. Each DSP slice has multipliers and adder/accumulators, which are the building blocks for complex signal processing capabilities.

The LatticeECP3 devices feature up to 16 embedded 3.2 Gbps SERDES (Serializer / Deserializer) channels. Each SERDES channel contains independent 8b/10b encoding / decoding, polarity adjust and elastic buffer logic. Each group of four SERDES channels, along with its Physical Coding Sub-layer (PCS) block, creates a quad. The functionality of the SERDES/PCS quads can be controlled by memory cells set during device configuration or by registers that are addressable during device operation. The registers in every quad can be programmed via the SERDES Client Interface (SCI). These quads (up to four) are located at the bottom of the devices.

Each PIC block encompasses two PIOs (PIO pairs) with their respective sysl/O buffers. The sysl/O buffers of the LatticeECP3 devices are arranged in seven banks, allowing the implementation of a wide variety of I/O standards. In addition, a separate I/O bank is provided for the programming interfaces. 50% of the PIO pairs on the left and right edges of the device can be configured as LVDS transmit/receive pairs. The PIC logic also includes pre-engineered support to aid in the implementation of high speed source synchronous standards such as XGMII, 7:1 LVDS, along with memory interfaces including DDR3.

The LatticeECP3 registers in PFU and sysl/O can be configured to be SET or RESET. After power up and the device is configured, it enters into user mode with these registers SET/RESET according to the configuration setting, allowing the device entering to a known state for predictable system function.

Other blocks provided include PLLs, DLLs and configuration functions. The LatticeECP3 architecture provides two Delay Locked Loops (DLLs) and up to ten Phase Locked Loops (PLLs). The PLL and DLL blocks are located at the end of the EBR/DSP rows.

The configuration block that supports features such as configuration bit-stream decryption, transparent updates and dual-boot support is located toward the center of this EBR row. Every device in the LatticeECP3 family supports a sysCONFIG<sup>™</sup> port located in the corner between banks one and two, which allows for serial or parallel device configuration.

In addition, every device in the family has a JTAG port. This family also provides an on-chip oscillator and soft error detect capability. The LatticeECP3 devices use 1.2 V as their core voltage.

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## Modes of Operation

Each slice has up to four potential modes of operation: Logic, Ripple, RAM and ROM.

#### Logic Mode

In this mode, the LUTs in each slice are configured as 4-input combinatorial lookup tables. A LUT4 can have 16 possible input combinations. Any four input logic functions can be generated by programming this lookup table. Since there are two LUT4s per slice, a LUT5 can be constructed within one slice. Larger look-up tables such as LUT6, LUT7 and LUT8 can be constructed by concatenating other slices. Note LUT8 requires more than four slices.

#### **Ripple Mode**

Ripple mode supports the efficient implementation of small arithmetic functions. In ripple mode, the following functions can be implemented by each slice:

- Addition 2-bit
- Subtraction 2-bit
- Add/Subtract 2-bit using dynamic control
- Up counter 2-bit
- Down counter 2-bit
- Up/Down counter with asynchronous clear
- Up/Down counter with preload (sync)
- Ripple mode multiplier building block
- Multiplier support
- Comparator functions of A and B inputs
  - A greater-than-or-equal-to B
  - A not-equal-to B
  - A less-than-or-equal-to B

Ripple Mode includes an optional configuration that performs arithmetic using fast carry chain methods. In this configuration (also referred to as CCU2 mode) two additional signals, Carry Generate and Carry Propagate, are generated on a per slice basis to allow fast arithmetic functions to be constructed by concatenating Slices.

#### RAM Mode

In this mode, a 16x4-bit distributed single port RAM (SPR) can be constructed using each LUT block in Slice 0 and Slice 1 as a 16x1-bit memory. Slice 2 is used to provide memory address and control signals. A 16x2-bit pseudo dual port RAM (PDPR) memory is created by using one Slice as the read-write port and the other companion slice as the read-only port.

LatticeECP3 devices support distributed memory initialization.

The Lattice design tools support the creation of a variety of different size memories. Where appropriate, the software will construct these using distributed memory primitives that represent the capabilities of the PFU. Table 2-3 shows the number of slices required to implement different distributed RAM primitives. For more information about using RAM in LatticeECP3 devices, please see TN1179, LatticeECP3 Memory Usage Guide.

#### Table 2-3. Number of Slices Required to Implement Distributed RAM

	SPR 16X4	PDPR 16X4
Number of slices	3	3

Note: SPR = Single Port RAM, PDPR = Pseudo Dual Port RAM



chain in order to better match the reference and feedback signals. This digital code from the ALU is also transmitted via the Digital Control bus (DCNTL) bus to its associated Slave Delay lines (two per DLL). The ALUHOLD input allows the user to suspend the ALU output at its current value. The UDDCNTL signal allows the user to latch the current value on the DCNTL bus.

The DLL has two clock outputs, CLKOP and CLKOS. These outputs can individually select one of the outputs from the tapped delay line. The CLKOS has optional fine delay shift and divider blocks to allow this output to be further modified, if required. The fine delay shift block allows the CLKOS output to phase shifted a further 45, 22.5 or 11.25 degrees relative to its normal position. Both the CLKOS and CLKOP outputs are available with optional duty cycle correction. Divide by two and divide by four frequencies are available at CLKOS. The LOCK output signal is asserted when the DLL is locked. Figure 2-5 shows the DLL block diagram and Table 2-5 provides a description of the DLL inputs and outputs.

The user can configure the DLL for many common functions such as time reference delay mode and clock injection removal mode. Lattice provides primitives in its design tools for these functions.



Figure 2-5. Delay Locked Loop Diagram (DLL)

\* This signal is not user accessible. This can only be used to feed the slave delay line.



#### Figure 2-8. Clock Divider Connections



## **Clock Distribution Network**

LatticeECP3 devices have eight quadrant-based primary clocks and eight secondary clock/control sources. Two high performance edge clocks are available on the top, left, and right edges of the device to support high speed interfaces. These clock sources are selected from external I/Os, the sysCLOCK PLLs, DLLs or routing. These clock sources are fed throughout the chip via a clock distribution system.

## **Primary Clock Sources**

LatticeECP3 devices derive clocks from six primary source types: PLL outputs, DLL outputs, CLKDIV outputs, dedicated clock inputs, routing and SERDES Quads. LatticeECP3 devices have two to ten sysCLOCK PLLs and two DLLs, located on the left and right sides of the device. There are six dedicated clock inputs: two on the top side, two on the left side and two on the right side of the device. Figures 2-9, 2-10 and 2-11 show the primary clock sources for LatticeECP3 devices.

#### Figure 2-9. Primary Clock Sources for LatticeECP3-17



Note: Clock inputs can be configured in differential or single-ended mode.



#### Figure 2-16. Per Region Secondary Clock Selection



### **Slice Clock Selection**

Figure 2-17 shows the clock selections and Figure 2-18 shows the control selections for Slice0 through Slice2. All the primary clocks and seven secondary clocks are routed to this clock selection mux. Other signals can be used as a clock input to the slices via routing. Slice controls are generated from the secondary clocks/controls or other signals connected via routing.

If none of the signals are selected for both clock and control then the default value of the mux output is 1. Slice 3 does not have any registers; therefore it does not have the clock or control muxes.

#### Figure 2-17. Slice0 through Slice2 Clock Selection



Figure 2-18. Slice0 through Slice2 Control Selection





The edge clocks on the top, left, and right sides of the device can drive the secondary clocks or general routing resources of the device. The left and right side edge clocks also can drive the primary clock network through the clock dividers (CLKDIV).

## sysMEM Memory

LatticeECP3 devices contain a number of sysMEM Embedded Block RAM (EBR). The EBR consists of an 18-Kbit RAM with memory core, dedicated input registers and output registers with separate clock and clock enable. Each EBR includes functionality to support true dual-port, pseudo dual-port, single-port RAM, ROM and FIFO buffers (via external PFUs).

## sysMEM Memory Block

The sysMEM block can implement single port, dual port or pseudo dual port memories. Each block can be used in a variety of depths and widths as shown in Table 2-7. FIFOs can be implemented in sysMEM EBR blocks by implementing support logic with PFUs. The EBR block facilitates parity checking by supporting an optional parity bit for each data byte. EBR blocks provide byte-enable support for configurations with18-bit and 36-bit data widths. For more information, please see TN1179, LatticeECP3 Memory Usage Guide.

#### Table 2-7. sysMEM Block Configurations

Memory Mode	Configurations
Single Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18 512 x 36
True Dual Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18
Pseudo Dual Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18 512 x 36

## Bus Size Matching

All of the multi-port memory modes support different widths on each of the ports. The RAM bits are mapped LSB word 0 to MSB word 0, LSB word 1 to MSB word 1, and so on. Although the word size and number of words for each port varies, this mapping scheme applies to each port.

## **RAM Initialization and ROM Operation**

If desired, the contents of the RAM can be pre-loaded during device configuration. By preloading the RAM block during the chip configuration cycle and disabling the write controls, the sysMEM block can also be utilized as a ROM.

## Memory Cascading

Larger and deeper blocks of RAM can be created using EBR sysMEM Blocks. Typically, the Lattice design tools cascade memory transparently, based on specific design inputs.



### Single, Dual and Pseudo-Dual Port Modes

In all the sysMEM RAM modes the input data and address for the ports are registered at the input of the memory array. The output data of the memory is optionally registered at the output.

EBR memory supports the following forms of write behavior for single port or dual port operation:

- 1. **Normal** Data on the output appears only during a read cycle. During a write cycle, the data (at the current address) does not appear on the output. This mode is supported for all data widths.
- 2. Write Through A copy of the input data appears at the output of the same port during a write cycle. This mode is supported for all data widths.
- 3. **Read-Before-Write (EA devices only)** When new data is written, the old content of the address appears at the output. This mode is supported for x9, x18, and x36 data widths.

#### Memory Core Reset

The memory array in the EBR utilizes latches at the A and B output ports. These latches can be reset asynchronously or synchronously. RSTA and RSTB are local signals, which reset the output latches associated with Port A and Port B, respectively. The Global Reset (GSRN) signal can reset both ports. The output data latches and associated resets for both ports are as shown in Figure 2-22.

#### Figure 2-22. Memory Core Reset



For further information on the sysMEM EBR block, please see the list of technical documentation at the end of this data sheet.

## sysDSP<sup>™</sup> Slice

The LatticeECP3 family provides an enhanced sysDSP architecture, making it ideally suited for low-cost, high-performance Digital Signal Processing (DSP) applications. Typical functions used in these applications are Finite Impulse Response (FIR) filters, Fast Fourier Transforms (FFT) functions, Correlators, Reed-Solomon/Turbo/Convolution encoders and decoders. These complex signal processing functions use similar building blocks such as multiply-adders and multiply-accumulators.

## sysDSP Slice Approach Compared to General DSP

Conventional general-purpose DSP chips typically contain one to four (Multiply and Accumulate) MAC units with fixed data-width multipliers; this leads to limited parallelism and limited throughput. Their throughput is increased by higher clock speeds. The LatticeECP3, on the other hand, has many DSP slices that support different data widths.



### MAC DSP Element

In this case, the two operands, AA and AB, are multiplied and the result is added with the previous accumulated value. This accumulated value is available at the output. The user can enable the input and pipeline registers, but the output register is always enabled. The output register is used to store the accumulated value. The ALU is configured as the accumulator in the sysDSP slice in the LatticeECP3 family can be initialized dynamically. A registered overflow signal is also available. The overflow conditions are provided later in this document. Figure 2-27 shows the MAC sysDSP element.

#### Figure 2-27. MAC DSP Element





## **Control Logic Block**

The control logic block allows the selection and modification of control signals for use in the PIO block.

## **DDR Memory Support**

Certain PICs have additional circuitry to allow the implementation of high-speed source synchronous and DDR, DDR2 and DDR3 memory interfaces. The support varies by the edge of the device as detailed below.

## Left and Right Edges

The left and right sides of the PIC have fully functional elements supporting DDR, DDR2, and DDR3 memory interfaces. One of every 12 PIOs supports the dedicated DQS pins with the DQS control logic block. Figure 2-35 shows the DQS bus spanning 11 I/O pins. Two of every 12 PIOs support the dedicated DQS and DQS# pins with the DQS control logic block.

## **Bottom Edge**

PICs on the bottom edge of the device do not support DDR memory and Generic DDR interfaces.

## Top Edge

PICs on the top side are similar to the PIO elements on the left and right sides but do not support gearing on the output registers. Hence, the modes to support output/tristate DDR3 memory are removed on the top side.

The exact DQS pins are shown in a dual function in the Logic Signal Connections table in this data sheet. Additional detail is provided in the Signal Descriptions table. The DQS signal from the bus is used to strobe the DDR data from the memory into input register blocks. Interfaces on the left, right and top edges are designed for DDR memories that support 10 bits of data.

	PIO A	<b>↓</b>	PADA "T"
	PIO B		PADB "C"
	PIO A		PADA "T"
	PIO B	+	PADB "C"
	PIO A		PADA "T"
	PIO B	L+	PADB "C"
_ DQS	PIO A	SysIO Buffer Delay ◀	PADA "T" LVDS Pair
	PIO B		PADB "C"
	PIO A		PADA "T" LVDS Pair
	→ PIO A → PIO B		PADA "T" LVDS Pair PADB "C"
	→ PIO A → PIO B → PIO A		PADA "T" LVDS Pair PADB "C" PADA "T" LVDS Pair
			PADA "T" LVDS Pair PADB "C" PADA "T" LVDS Pair PADB "C"

#### Figure 2-35. DQS Grouping on the Left, Right and Top Edges



Package	ECP3-17	ECP3-35	ECP3-70	ECP3-95	ECP3-150
256 ftBGA	1	1	—	—	—
328 csBGA	2 channels	—	—	—	—
484 fpBGA	1	1	1	1	
672 fpBGA	—	1	2	2	2
1156 fpBGA	—	—	3	3	4

## SERDES Block

A SERDES receiver channel may receive the serial differential data stream, equalize the signal, perform Clock and Data Recovery (CDR) and de-serialize the data stream before passing the 8- or 10-bit data to the PCS logic. The SERDES transmitter channel may receive the parallel 8- or 10-bit data, serialize the data and transmit the serial bit stream through the differential drivers. Figure 2-41 shows a single-channel SERDES/PCS block. Each SERDES channel provides a recovered clock and a SERDES transmit clock to the PCS block and to the FPGA core logic.

Each transmit channel, receiver channel, and SERDES PLL shares the same power supply (VCCA). The output and input buffers of each channel have their own independent power supplies (VCCOB and VCCIB).

Figure 2-41. Simplified Channel Block Diagram for SERDES/PCS Block



## PCS

As shown in Figure 2-41, the PCS receives the parallel digital data from the deserializer and selects the polarity, performs word alignment, decodes (8b/10b), provides Clock Tolerance Compensation and transfers the clock domain from the recovered clock to the FPGA clock via the Down Sample FIFO.

For the transmit channel, the PCS block receives the parallel data from the FPGA core, encodes it with 8b/10b, selects the polarity and passes the 8/10 bit data to the transmit SERDES channel.

The PCS also provides bypass modes that allow a direct 8-bit or 10-bit interface from the SERDES to the FPGA logic. The PCS interface to the FPGA can also be programmed to run at 1/2 speed for a 16-bit or 20-bit interface to the FPGA logic.



## sysI/O Differential Electrical Characteristics LVDS25

Parameter	Description	Test Conditions	Min.	Тур.	Max.	Units
V <sub>INP</sub> <sup>1</sup> , V <sub>INM</sub> <sup>1</sup>	Input Voltage		0	_	2.4	V
V <sub>CM</sub> <sup>1</sup>	Input Common Mode Voltage	Half the Sum of the Two Inputs	0.05	_	2.35	V
V <sub>THD</sub>	Differential Input Threshold	Difference Between the Two Inputs	+/-100	_	_	mV
I <sub>IN</sub>	Input Current	Power On or Power Off		_	+/-10	μΑ
V <sub>OH</sub>	Output High Voltage for $V_{OP}$ or $V_{OM}$	R <sub>T</sub> = 100 Ohm		1.38	1.60	V
V <sub>OL</sub>	Output Low Voltage for $V_{OP}$ or $V_{OM}$	R <sub>T</sub> = 100 Ohm	0.9 V	1.03	_	V
V <sub>OD</sub>	Output Voltage Differential	(V <sub>OP</sub> - V <sub>OM</sub> ), R <sub>T</sub> = 100 Ohm	250	350	450	mV
$\Delta V_{OD}$	Change in V <sub>OD</sub> Between High and Low		_	_	50	mV
V <sub>OS</sub>	Output Voltage Offset	$(V_{OP} + V_{OM})/2, R_{T} = 100 \text{ Ohm}$	1.125	1.20	1.375	V
$\Delta V_{OS}$	Change in V <sub>OS</sub> Between H and L		_	_	50	mV
I <sub>SAB</sub>	Output Short Circuit Current	V <sub>OD</sub> = 0V Driver Outputs Shorted to Each Other	_	_	12	mA

1, On the left and right sides of the device, this specification is valid only for  $V_{CCIO} = 2.5$  V or 3.3 V.

## **Differential HSTL and SSTL**

Differential HSTL and SSTL outputs are implemented as a pair of complementary single-ended outputs. All allowable single-ended output classes (class I and class II) are supported in this mode.



## MLVDS25

The LatticeECP3 devices support the differential MLVDS standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The MLVDS input standard is supported by the LVDS differential input buffer. The scheme shown in Figure 3-5 is one possible solution for MLVDS standard implementation. Resistor values in Figure 3-5 are industry standard values for 1% resistors.





Table 3-5. MLVDS25 DC Conditions<sup>1</sup>

		Typical		
Parameter	Description	<b>Ζο=50</b> Ω	<b>Ζο=70</b> Ω	Units
V <sub>CCIO</sub>	Output Driver Supply (+/-5%)	2.50	2.50	V
Z <sub>OUT</sub>	Driver Impedance	10.00	10.00	Ω
R <sub>S</sub>	Driver Series Resistor (+/-1%)	35.00	35.00	Ω
R <sub>TL</sub>	Driver Parallel Resistor (+/-1%)	50.00	70.00	Ω
R <sub>TR</sub>	Receiver Termination (+/-1%)	50.00	70.00	Ω
V <sub>OH</sub>	Output High Voltage	1.52	1.60	V
V <sub>OL</sub>	Output Low Voltage	0.98	0.90	V
V <sub>OD</sub>	Output Differential Voltage	0.54	0.70	V
V <sub>CM</sub>	Output Common Mode Voltage	1.25	1.25	V
I <sub>DC</sub>	DC Output Current	21.74	20.00	mA

1. For input buffer, see LVDS table.



# LatticeECP3 Internal Switching Characteristics<sup>1, 2, 5</sup>

		-8		-7		-6		
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units.
PFU/PFF Logic Mode Timing								
t <sub>LUT4_PFU</sub>	LUT4 delay (A to D inputs to F output)	_	0.147	_	0.163	_	0.179	ns
t <sub>LUT6_PFU</sub>	LUT6 delay (A to D inputs to OFX output)	—	0.281		0.335	_	0.379	ns
t <sub>LSR_PFU</sub>	Set/Reset to output of PFU (Asynchronous)	—	0.593	—	0.674	—	0.756	ns
t <sub>LSRREC_PFU</sub>	Asynchronous Set/Reset recovery time for PFU Logic		0.298		0.345		0.391	ns
t <sub>SUM_PFU</sub>	Clock to Mux (M0,M1) Input Setup Time	0.134	_	0.144	_	0.153		ns
t <sub>HM_PFU</sub>	Clock to Mux (M0,M1) Input Hold Time	-0.097	_	-0.103	_	-0.109	_	ns
t <sub>SUD_PFU</sub>	Clock to D input setup time	0.061	_	0.068	_	0.075		ns
t <sub>HD_PFU</sub>	Clock to D input hold time	0.019	_	0.013	_	0.015		ns
t <sub>CK2Q_PFU</sub>	Clock to Q delay, (D-type Register Configuration)	_	0.243	_	0.273	_	0.303	ns
PFU Dual Port	Memory Mode Timing							
t <sub>CORAM_PFU</sub>	Clock to Output (F Port)	—	0.710	—	0.803	—	0.897	ns
t <sub>SUDATA_PFU</sub>	Data Setup Time	-0.137	_	-0.155	_	-0.174		ns
t <sub>HDATA_PFU</sub>	Data Hold Time	0.188	_	0.217	_	0.246	_	ns
t <sub>SUADDR_PFU</sub>	Address Setup Time	-0.227	_	-0.257	_	-0.286		ns
t <sub>HADDR_PFU</sub>	Address Hold Time	0.240	_	0.275	_	0.310	_	ns
t <sub>SUWREN_PFU</sub>	Write/Read Enable Setup Time	-0.055		-0.055	_	-0.063	_	ns
t <sub>HWREN_</sub> PFU	Write/Read Enable Hold Time	0.059	_	0.059	_	0.071	_	ns
PIC Timing								
PIO Input/Out	out Buffer Timing							
t <sub>IN_PIO</sub>	Input Buffer Delay (LVCMOS25)		0.423		0.466		0.508	ns
t <sub>OUT_PIO</sub>	Output Buffer Delay (LVCMOS25)	—	1.241	_	1.301	_	1.361	ns
IOLOGIC Inpu	t/Output Timing							
t <sub>SUI_PIO</sub>	Input Register Setup Time (Data Before Clock)	0.956		1.124		1.293		ns
t <sub>HI_PIO</sub>	Input Register Hold Time (Data after Clock)	0.225		0.184		0.240		ns
t <sub>COO_PIO</sub>	Output Register Clock to Output Delay <sup>4</sup>	-	1.09	-	1.16	-	1.23	ns
t <sub>SUCE_PIO</sub>	Input Register Clock Enable Setup Time	0.220	_	0.185	_	0.150	_	ns
t <sub>HCE_PIO</sub>	Input Register Clock Enable Hold Time	-0.085		-0.072		-0.058		ns
t <sub>SULSR_PIO</sub>	Set/Reset Setup Time	0.117	_	0.103	_	0.088	_	ns
t <sub>HLSR_PIO</sub>	Set/Reset Hold Time	-0.107	_	-0.094	_	-0.081	_	ns
EBR Timing								
t <sub>CO_EBR</sub>	Clock (Read) to output from Address or Data	—	2.78	—	2.89	—	2.99	ns
t <sub>COO_EBR</sub>	Clock (Write) to output from EBR output Register	—	0.31	—	0.32	—	0.33	ns
t <sub>SUDATA_EBR</sub>	Setup Data to EBR Memory	-0.218	_	-0.227	_	-0.237	_	ns
t <sub>HDATA_EBR</sub>	Hold Data to EBR Memory	0.249		0.257		0.265	—	ns
t <sub>SUADDR_EBR</sub>	Setup Address to EBR Memory	-0.071		-0.070		-0.068		ns
t <sub>HADDR_EBR</sub>	Hold Address to EBR Memory	0.118		0.098		0.077		ns
t <sub>SUWREN_EBR</sub>	Setup Write/Read Enable to EBR Memory	-0.107	_	-0.106	_	-0.106	—	ns

## **Over Recommended Commercial Operating Conditions**



### Figure 3-19. Test Loads

Test Loads









## LatticeECP3 sysCONFIG Port Timing Specifications

Parameter	Description			Max.	Units
POR, Confi	guration Initialization, and Wakeup				1
	Time from the Application of $V_{CC}$ , $V_{CCAUX}$ or $V_{CCIO8}^{*}$ (Whichever	Master mode		23	ms
t <sub>ICFG</sub>	is the Last to Cross the POR Trip Point) to the Rising Edge of INITN	Slave mode	—	6	ms
t <sub>VMC</sub>	Time from t <sub>ICFG</sub> to the Valid Master MCLK	—	5	μs	
t <sub>PRGM</sub>	PROGRAMN Low Time to Start Configuration		25	—	ns
t <sub>PRGMRJ</sub>	PROGRAMN Pin Pulse Rejection		—	10	ns
t <sub>DPPINIT</sub>	Delay Time from PROGRAMN Low to INITN Low		—	37	ns
t <sub>DPPDONE</sub>	Delay Time from PROGRAMN Low to DONE Low		_	37	ns
t <sub>DINIT</sub> 1	PROGRAMN High to INITN High Delay		—	1	ms
t <sub>MWC</sub>	Additional Wake Master Clock Signals After DONE Pin is High		100	500	cycles
t <sub>CZ</sub>	MCLK From Active To Low To High-Z		—	300	ns
t <sub>IODISS</sub>	User I/O Disable from PROGRAMN Low			100	ns
t <sub>IOENSS</sub>	User I/O Enabled Time from CCLK Edge During Wake-up Sequer	nce		100	ns
All Configu	ration Modes				
t <sub>SUCDI</sub>	Data Setup Time to CCLK/MCLK		5	—	ns
t <sub>HCDI</sub>	Data Hold Time to CCLK/MCLK		1	—	ns
t <sub>CODO</sub>	CCLK/MCLK to DOUT in Flowthrough Mode		-0.2	12	ns
Slave Seria	l				1
t <sub>SSCH</sub>	CCLK Minimum High Pulse	5	—	ns	
t <sub>SSCL</sub>	CCLK Minimum Low Pulse	5	_	ns	
	Without encryption				MHz
ICCLK	CCLK Frequency With encryption			20	MHz
Master and Slave Parallel					
t <sub>SUCS</sub>	CSN[1:0] Setup Time to CCLK/MCLK		7	—	ns
t <sub>HCS</sub>	CSN[1:0] Hold Time to CCLK/MCLK		1	—	ns
t <sub>SUWD</sub>	WRITEN Setup Time to CCLK/MCLK		7	_	ns
t <sub>HWD</sub>	WRITEN Hold Time to CCLK/MCLK		1	_	ns
t <sub>DCB</sub>	CCLK/MCLK to BUSY Delay Time		_	12	ns
t <sub>CORD</sub>	CCLK to Out for Read Data		_	12	ns
t <sub>BSCH</sub>	CCLK Minimum High Pulse		6	_	ns
t <sub>BSCL</sub>	CCLK Minimum Low Pulse		6	_	ns
t <sub>BSCYC</sub>	Byte Slave Cycle Time		30	—	ns
		Without encryption		33	MHz
<sup>†</sup> CCLK	CCLK/MCLK Frequency	With encryption		20	MHz
Master and	Slave SPI			1	1
t <sub>CFGX</sub>	INITN High to MCLK Low			80	ns
t <sub>CSSPI</sub>	INITN High to CSSPIN Low			2	μs
t <sub>SOCDO</sub>	MCLK Low to Output Valid			15	ns
t <sub>CSPID</sub>	CSSPIN[0:1] Low to First MCLK Edge Setup Time		0.3		μs
,		Without encryption		33	MHz
<sup>†</sup> CCLK	CCLK Frequency	With encryption		20	MHz
t <sub>SSCH</sub>	CCLK Minimum High Pulse		5	_	ns

### **Over Recommended Operating Conditions**



#### Figure 3-24. Power-On-Reset (POR) Timing



Time taken from V<sub>CC</sub>, V<sub>CCAUX</sub> or V<sub>CCIO8</sub>, whichever is the last to cross the POR trip point.
 Device is in a Master Mode (SPI, SPIm).
 The CFG pins are normally static (hard wired).



#### Figure 3-25. sysCONFIG Port Timing



## Point-to-Point LVDS (PPLVDS)

#### Over Recommended Operating Conditions

Description	Min.	Тур.	Max.	Units
Output driver supply $(1/-5\%)$	3.14	3.3	3.47	V
	2.25	2.5	2.75	V
Input differential voltage	100	—	400	mV
Input common mode voltage	0.2	—	2.3	V
Output differential voltage	130	—	400	mV
Output common mode voltage	0.5	0.8	1.4	V

### RSDS

#### **Over Recommended Operating Conditions**

Parameter Symbol	Description	Min.	Тур.	Max.	Units
V <sub>OD</sub>	Output voltage, differential, R <sub>T</sub> = 100 Ohms	100	200	600	mV
V <sub>OS</sub>	Output voltage, common mode	0.5	1.2	1.5	V
I <sub>RSDS</sub>	Differential driver output current	1	2	6	mA
V <sub>THD</sub>	Input voltage differential	100	—	-	mV
V <sub>CM</sub>	Input common mode voltage	0.3	—	1.5	V
T <sub>R</sub> , T <sub>F</sub>	Output rise and fall times, 20% to 80%	—	500		ps
T <sub>ODUTY</sub>	Output clock duty cycle	35	50	65	%

Note: Data is for 2 mA drive. Other differential driver current options are available.



## PICs and DDR Data (DQ) Pins Associated with the DDR Strobe (DQS) Pin

PICs Associated with DQS Strobe	PIO Within PIC	DDR Strobe (DQS) and Data (DQ) Pins						
For Left and Right Edges of the Device								
D[Edgo] [n 2]	А	DQ						
	В	DQ						
P[Edge] [n-2]	А	DQ						
	В	DQ						
D[Edgo] [n 1]	А	DQ						
	В	DQ						
P[Edge] [n]	А	[Edge]DQSn						
	В	DQ						
P[Edge] [n 1]	А	DQ						
	В	DQ						
D[Edgo] [n 2]	А	DQ						
r[Euge][II+2]	В	DQ						
For Top Edge of the Device								
P[Edge] [n-3]	А	DQ						
	В	DQ						
P[Edge] [n-2]	А	DQ						
	В	DQ						
P[Edge] [n-1]	А	DQ						
	В	DQ						
P[Edge] [n]	А	[Edge]DQSn						
i [⊏uge] [ii]	В	DQ						
P[Edge] [n+1]	А	DQ						
i [Euge] [iit i]	В	DQ						
P[Edge] [n 2]	А	DQ						
י נבטשכן נוידבן	В	DQ						

Note: "n" is a row PIC number.



# Pin Information Summary (Cont.)

Pin Information Summary		ECP3-95EA			ECP3-150EA		
Pin Type		484 fpBGA	672 fpBGA	1156 fpBGA	672 fpBGA	1156 fpBGA	
	Bank 0	42	60	86	60	94	
	Bank 1	36	48	78	48	86	
	Bank 2	24	34	36	34	58	
General Purpose	Bank 3	54	59	86	59	104	
	Bank 6	63	67	86	67	104	
	Bank 7	36	48	54	48	76	
	Bank 8	24	24	24	24	24	
	Bank 0	0	0	0	0	0	
	Bank 1	0	0	0	0	0	
	Bank 2	4	8	8	8	8	
General Purpose Inputs per	Bank 3	4	12	12	12	12	
Dank	Bank 6	4	12	12	12	12	
	Bank 7	4	8	8	8	8	
	Bank 8	0	0	0	0	0	
	Bank 0	0	0	0	0	0	
	Bank 1	0	0	0	0	0	
	Bank 2	0	0	0	0	0	
General Purpose Outputs per	Bank 3	0	0	0	0	0	
Dank	Bank 6	0	0	0	0	0	
	Bank 7	0	0	0	0	0	
	Bank 8	0	0	0	0	0	
Total Single-Ended User I/O		295	380	490	380	586	
VCC		16	32	32	32	32	
VCCAUX		8	12	16	12	16	
VTT		4	4	8	4	8	
VCCA		4	8	16	8	16	
VCCPLL		4	4	4	4	4	
	Bank 0	2	4	4	4	4	
	Bank 1	2	4	4	4	4	
	Bank 2	2	4	4	4	4	
VCCIO	Bank 3	2	4	4	4	4	
	Bank 6	2	4	4	4	4	
	Bank 7	2	4	4	4	4	
	Bank 8	2	2	2	2	2	
VCCJ		1	1	1	1	1	
ТАР		4	4	4	4	4	
GND, GNDIO		98	139	233	139	233	
NC		0	0	238	0	116	
Reserved <sup>1</sup>		2	2	2	2	2	
SERDES		26	52	78	52	104	
Miscellaneous Pins		8	8	8	8	8	
Total Bonded Pins		484	672	1156	672	1156	



Part Number	Voltage	Grade <sup>1</sup>	Power	Package	Pins	Temp.	LUTs (K)
LFE3-70EA-6FN484C	1.2 V	-6	STD	Lead-Free fpBGA	484	COM	67
LFE3-70EA-7FN484C	1.2 V	-7	STD	Lead-Free fpBGA	484	COM	67
LFE3-70EA-8FN484C	1.2 V	-8	STD	Lead-Free fpBGA	484	COM	67
LFE3-70EA-6LFN484C	1.2 V	-6	LOW	Lead-Free fpBGA	484	COM	67
LFE3-70EA-7LFN484C	1.2 V	-7	LOW	Lead-Free fpBGA	484	COM	67
LFE3-70EA-8LFN484C	1.2 V	-8	LOW	Lead-Free fpBGA	484	COM	67
LFE3-70EA-6FN672C	1.2 V	-6	STD	Lead-Free fpBGA	672	COM	67
LFE3-70EA-7FN672C	1.2 V	-7	STD	Lead-Free fpBGA	672	COM	67
LFE3-70EA-8FN672C	1.2 V	-8	STD	Lead-Free fpBGA	672	COM	67
LFE3-70EA-6LFN672C	1.2 V	-6	LOW	Lead-Free fpBGA	672	COM	67
LFE3-70EA-7LFN672C	1.2 V	-7	LOW	Lead-Free fpBGA	672	COM	67
LFE3-70EA-8LFN672C	1.2 V	-8	LOW	Lead-Free fpBGA	672	COM	67
LFE3-70EA-6FN1156C	1.2 V	-6	STD	Lead-Free fpBGA	1156	COM	67
LFE3-70EA-7FN1156C	1.2 V	-7	STD	Lead-Free fpBGA	1156	COM	67
LFE3-70EA-8FN1156C	1.2 V	-8	STD	Lead-Free fpBGA	1156	COM	67
LFE3-70EA-6LFN1156C	1.2 V	-6	LOW	Lead-Free fpBGA	1156	COM	67
LFE3-70EA-7LFN1156C	1.2 V	-7	LOW	Lead-Free fpBGA	1156	COM	67
LFE3-70EA-8LFN1156C	1.2 V	-8	LOW	Lead-Free fpBGA	1156	COM	67

1. For ordering information on -9 speed grade devices, please contact your Lattice Sales Representative.

Part Number	Voltage	Grade <sup>1</sup>	Power	Package	Pins	Temp.	LUTs (K)
LFE3-95EA-6FN484C	1.2 V	-6	STD	Lead-Free fpBGA	484	COM	92
LFE3-95EA-7FN484C	1.2 V	-7	STD	Lead-Free fpBGA	484	COM	92
LFE3-95EA-8FN484C	1.2 V	-8	STD	Lead-Free fpBGA	484	COM	92
LFE3-95EA-6LFN484C	1.2 V	-6	LOW	Lead-Free fpBGA	484	COM	92
LFE3-95EA-7LFN484C	1.2 V	-7	LOW	Lead-Free fpBGA	484	COM	92
LFE3-95EA-8LFN484C	1.2 V	-8	LOW	Lead-Free fpBGA	484	COM	92
LFE3-95EA-6FN672C	1.2 V	-6	STD	Lead-Free fpBGA	672	COM	92
LFE3-95EA-7FN672C	1.2 V	-7	STD	Lead-Free fpBGA	672	COM	92
LFE3-95EA-8FN672C	1.2 V	-8	STD	Lead-Free fpBGA	672	COM	92
LFE3-95EA-6LFN672C	1.2 V	-6	LOW	Lead-Free fpBGA	672	COM	92
LFE3-95EA-7LFN672C	1.2 V	-7	LOW	Lead-Free fpBGA	672	COM	92
LFE3-95EA-8LFN672C	1.2 V	-8	LOW	Lead-Free fpBGA	672	COM	92
LFE3-95EA-6FN1156C	1.2 V	-6	STD	Lead-Free fpBGA	1156	COM	92
LFE3-95EA-7FN1156C	1.2 V	-7	STD	Lead-Free fpBGA	1156	COM	92
LFE3-95EA-8FN1156C	1.2 V	-8	STD	Lead-Free fpBGA	1156	COM	92
LFE3-95EA-6LFN1156C	1.2 V	-6	LOW	Lead-Free fpBGA	1156	COM	92
LFE3-95EA-7LFN1156C	1.2 V	-7	LOW	Lead-Free fpBGA	1156	COM	92
LFE3-95EA-8LFN1156C	1.2 V	-8	LOW	Lead-Free fpBGA	1156	COM	92

1. For ordering information on -9 speed grade devices, please contact your Lattice Sales Representative.